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APPLICATION NO.	FIL	NG DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/046,792	01/15/2002		Hidetaka Natsume	NECW 19.349	6481	
26304	7590	08/12/2004		EXAMINER		
KATTEN N 575 MADIS		ZAVIS ROSENM	nguyen, Joseph H			
NEW YORK, NY 10022-2585				ART UNIT	PAPER NUMBER	
	,			2815		

DATE MAILED: 08/12/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
	10/046,792	NATSUME, HIDETAKA
Office Action Summary	Examiner	Art Unit
	Joseph Nguyen	2815
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period vortices are provided to the provided by the office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).
Status		
1) Responsive to communication(s) filed on <u>08 Ju</u>	<u>uly 2004</u> .	
2a) ☐ This action is FINAL . 2b) ☑ This	action is non-final.	
3) Since this application is in condition for alloward closed in accordance with the practice under E		
Disposition of Claims		
4) ☐ Claim(s) 1-13 and 22-31 is/are pending in the 4a) Of the above claim(s) 1-31 is/are withdrawr 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 22,23,30 and 31 is/are rejected. 7) ☐ Claim(s) 24-29 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	n from consideration.	
Application Papers		
9) ☐ The specification is objected to by the Examine 10) ☐ The drawing(s) filed on 15 January 2002 is/are Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct	: a)⊠ accepted or b)☐ objected drawing(s) be held in abeyance. See	e 37 CFR 1.85(a).
11) The oath or declaration is objected to by the Ex		
Priority under 35 U.S.C. § 119	•	
a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Burea	is have been received. Is have been received in Applicati Inity documents have been receive In (PCT Rule 17.2(a)).	ion No ed in this National Stage
Attachment(s) 1) M Notice of References Cited (PTO-892)	4) 🔲 Interview Summary	(PTO-413)
 7) Notice of References Cited (PTO-992) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 	Paper No(s)/Mail D	

Application/Control Number: 10/046,792

Art Unit: 2815

DETAILED ACTION

Election/Restrictions

Applicant's election of claims 22-31 in the reply filed on 07/28/2004 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)). Therefore, claims 22-31 are prosecuted whereas claims 1-13 are withdrawn from consideration.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 22, 23, 30, 31 are rejected under 35 U.S.C. 102(e) as being anticipated by Shrivastava et al.

Regarding claim 22, Shrivastava et al discloses on figure 2a a static random access memory cell comprising a first diffusion region 18 on a semiconductor substrate 12; a second diffusion region 20 formed on said

semiconductor substrate; a first conductive layer 38 formed over said semiconductor substrate; an interlayer insulating film 48 formed on said semiconductor substrate, said interlayer insulating film having an opening 34a which exposes said first and second diffusion layers and said first conductive layer; a second conductive layer 62 formed in said opening; a dielectric layer 64 formed on said second conductive layer; and a third conductive layer 68 formed on said dielectric layer, whereby a capacitor is formed by said second and third conductive layers and said dielectric layer.

Regarding claim 23, Shrivastava et al discloses on figure 2a a first load transistor which has source and drain regions, one of which corresponds to said first diffusion region 18; and a first drive transistor has source and drain regions, one of which corresponds to said second diffusion region 20.

Regarding claim 30, Shrivastava et al discloses figure 2a wherein a top surface of said second conductive layer 62 is lower than that of said interlayer insulating film.

Regarding claim 31, Shrivastava et al discloses wherein said first conductive layer 38 is formed on an element isolation layer 16 on said semiconductor substrate.

Claims 22, 30 are rejected under 35 U.S.C. 102(b) as being anticipated by Jost et al or Narita.

With respect to Jost et al.

Regarding claims 22, 30, Jost et al discloses on figure 5 all the structures set forth in the claimed invention.

With respect to Narita.

Regarding claims 22, 30, Narita discloses on figure 1 all the structures set forth in the claimed invention.

Allowable Subject Matter

Claims 24-29 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Joseph Nguyen whose telephone number is (571) 272-1734. The examiner can normally be reached on Monday-Friday, 7:30 am- 4:30 pm. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306 for regular communications.

JN August 19, 2004

JEROME JACKSON PRIMARY EXAMINER